

## THE NEW HIGH SPEED-LOW POWER 3.3V 1Mb SRAM

The new and improved 1Mb 3.3V, 12ns, Low Power SRAM is being sampled now. There are two strategic factors behind this new product release. First and foremost, ISSI further reinforces its long term commitment to SRAM, at a time when other manufacturers are de-emphasizing this market. Secondly, our continuous strive for innovation resulted in a new die that delivers dramatically lower power characteristics.



	IS61WV6416BLL 64K x 16 High Speed	IS64WV6416BLL 64K x 16 High Speed	Comments	Chipset Interface
Temperature Support	Industrial	Automotive		TI
Technology	0.15 um 0.25 um (old die)	0.15 um	Smaller Die Size	Analog Devices Broadcom
Standby Current	50 uA* 10 mA (old die)	75 uA	Lower Current	Fujitsu
Operating Current	45 mA* 110 mA (old die)	50 mA	Lower Current	Agere FPGA
Packaging	TSOP-II, BGA	TSOP-II, BGA	Drop in	(Actel, Xilinx, Altera)
Speed	12 ns	15 ns		Other Chipsets
Lead Free and Non-Lead Free	YES	YES	RoHS Compliant	and ASICS
Status	Sampling	Sampling		

\* Typical operating current is 20mA and typical standby current is 6uA.

### Applications:

The device is used in a variety of applications including Consumer, Handheld/Wireless (battery backed), Industrial, Automotive, Telecom, and Networking.

### Competitive Analysis

	ISSI	Comp. A	Comp. B	Comp. C
Standby Current	50 uA	5,000 uA	3,000 uA	10,000 uA
Operating Current	45 mA	75 mA	60 mA	160 mA